Docket No.: 5882P060

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re the Application of:

CHOONG YONG SOHN, ET AL.

Application No.:

Filed:

For: Method of Forming a Buffer Dielectric Layer In A

Semiconductor Device and A Method of

Manufacturing a Thin Film Transistor Using the

Same

Art Group:

Examiner:

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

In accordance with the duty of disclosure, enclosed is a copy of Information Disclosure Statement by Applicant (form PTO/SB/08), which is being submitted concurrently with the Utility Application. It is respectfully requested that the cited references be considered and that the enclosed copy of PTO/SB/08 be initialed by the Examiner to indicate such consideration and a copy thereof returned to applicant(s).

-1- 5882P060

The submission of this Information Disclosure Statement is not to be construed as a representation that a search has been made in the subject application and is not to be construed as an admission that the information cited in this statement is material to patentability.

Please charge any fees due to Deposit Account 02-2666. A duplicate copy of the Fee Transmittal (PTO/SB/17) is enclosed for this purpose.

Respectfully submitted,

BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN LLP

Eric S. Hyman, Reg. No. 30,139

12400 Wilshire Blvd., 7th Floor Los Angeles, California 90025 (310) 207-3800

Date:

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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Complete if Known		
		Application Number		
		Filing Date		
		First Named Inventor	Choong Yong Sohn	
		Art Unit		
		Examiner Name		
Sheet	of	Attorney Docket Number	5882P060	

	U.S. PATENT DOCUMENTS				
		Document Number	Publication Date	Date	Pages Columns Lines Where
Examiner Initials*	Cite No.1	Number - Kind Code ² (if known)	er Icoue Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		US-5733641	03-31-1998	Fork et al.	
		US-			
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		US-			

	FOREIGN PATENT DOCUMENTS					
Examiner	Cite	Foreign Patent Document			Pages, Columns, Lines.	
Initials*	No.¹	Country Code ³ - Number ⁴ - Kind Code ⁵ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		1020000003176	01-15-2000	Hyundai Electronics Ind., Co., Ltd.		
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Signature	Considered	
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^{*}Examiner: tnitial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication.

¹Applicant's unique citation designation number (optional). ²See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to place a check mark here if English language Translation is attached.

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		Application Number			
		Filing Date			
		First Named Inventor	Choong Yong Sohn		
		Art Unit			
		Examiner Name			
Sheet	of	Attomey Docket Number	5882P060		

	NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No.¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²		
	•	SID 02 Digest, "High-Mobility Poly-Si TFTs Employing XeCl Eximer Laser Annealing on Selectively Floating a-Si thin Film", C. Kim et al., pages 905-907			
		Jpn. J. Appl. Phys. Vol. 38 (1999), pp L110-L112, "Preparation of Giant-Grain Seed Layer for Poly-Silicon Thin-Film Solar Cells", W. Yeh, et al.			
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Examine	- 1	Date	_		

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Examiner	Date	
Signature	Considered	

Based on PTO/SB/08B (08-03) as modified by Blakely, Solokoff, Taylor & Zafman (wlr) 08/11/2003. Send To: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450

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